

isc Silicon NPN Power Transistor

BUV40

DESCRIPTION

- Low Collector Saturation Voltage-
: $V_{CE(sat)} = 0.8V$ (Max.) @ $I_C = 5.5A$
- High Switching Speed

APPLICATIONS

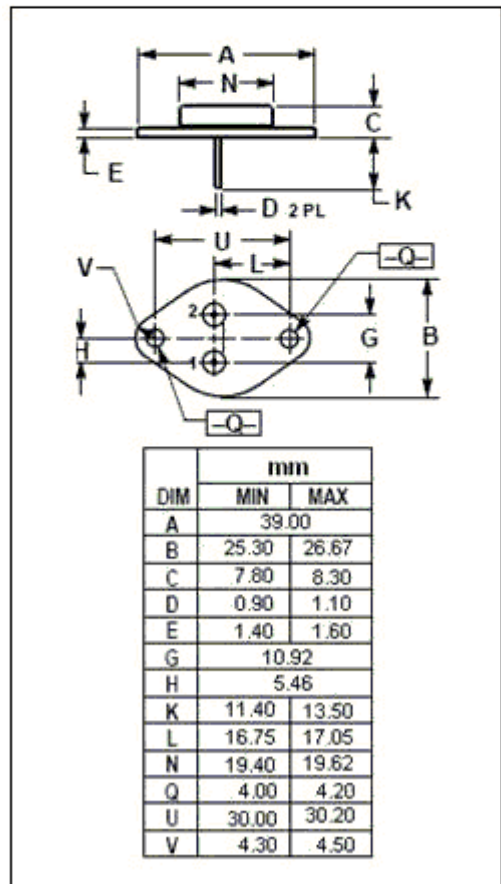
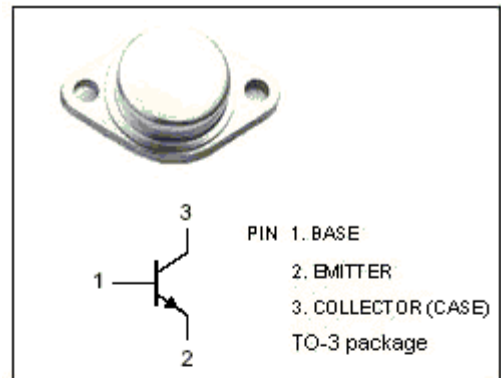
- Designed for high current, high speed, high power applications.

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CEV}	Collector-Emitter Voltage $V_{BE} = -1.5V$	250	V
V_{CEO}	Collector-Emitter Voltage	125	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	20	A
I_{CM}	Collector Current-Peak	30	A
I_B	Base Current-Continuous	4	A
I_{BM}	Base Current- Peak	6	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ C$	120	W
T_j	Junction Temperature	200	°C
T_{stg}	Storage Temperature Range	-65~200	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	1.46	°C/W



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=0.2\text{A}; I_B=0; L=25\text{mH}$	125			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=50\text{mA}; I_C=0$	7			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C=5.5\text{A}; I_B=0.275\text{A}$			0.8	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C=11\text{A}; I_B=1.1\text{A}$			0.9	V
$V_{CE(sat)-3}$	Collector-Emitter Saturation Voltage	$I_C=15\text{A}; I_B=1.875\text{A}$			1.2	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	$I_C=11\text{A}; I_B=1.1\text{A}$			1.6	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage	$I_C=15\text{A}; I_B=1.875\text{A}$			1.9	V
I_{CER}	Collector Cutoff Current	$V_{CE}=250\text{V}; R_{BE}=10\ \Omega$ $V_{CE}=250\text{V}; R_{BE}=10\ \Omega; T_C=100^{\circ}\text{C}$			1.0 5.0	mA
I_{CEV}	Collector Cutoff Current	$V_{CE}=250\text{V}; V_{BE}=-1.5\text{V}$ $V_{CE}=250\text{V}; V_{BE}=-1.5\text{V}; T_C=100^{\circ}\text{C}$			1.0 5.0	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			1.0	mA

Switching Times, Resistive Load

t_r	Rise Time	$I_C=15\text{A}; I_{B1}=1.8\text{A}; V_{CC}=100\text{V};$ $R_{B2}=1.3\ \Omega; V_{BB}=-5\text{V}; t_p=30\ \mu\text{s}$			1.0	μs
t_s	Storage Time				1.0	μs
t_f	Fall Time				0.3	μs